

SOT-23 Plastic-Encapsulate Transistors

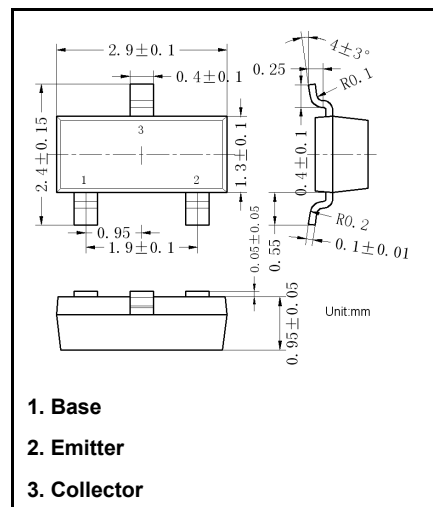
A1015 PNP Transistors

Features

■ Power dissipation

P_{CM} : 0.2W ($T_{amb} = 25^{\circ}C$)

Marking: BA



Maximum Ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-50	V
V_{CEO}	Collector Emitter Voltage	-45	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current- Continuous	-0.1	A
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55 ~ +150	$^{\circ}C$

Electrical Characteristics ($T_a=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu A, I_E = 0$	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -1mA, I_B = 0$	-45			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu A, I_C = 0$	-5			V
I_{CBO}	Collector cut-off current	$V_{CB} = -50V, I_E = 0$			-100	nA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5V, I_C = 0$			-100	nA
h_{FE}	DC current gain	$V_{CE} = -6V, I_C = -2mA$	200		1000	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = -100mA, I_B = -10mA$			-1.0	V
f_T	Transition frequency	$V_{CE} = -5V, I_C = -10mA, f = 30MHz$	150			MHz

Typical Characteristics

